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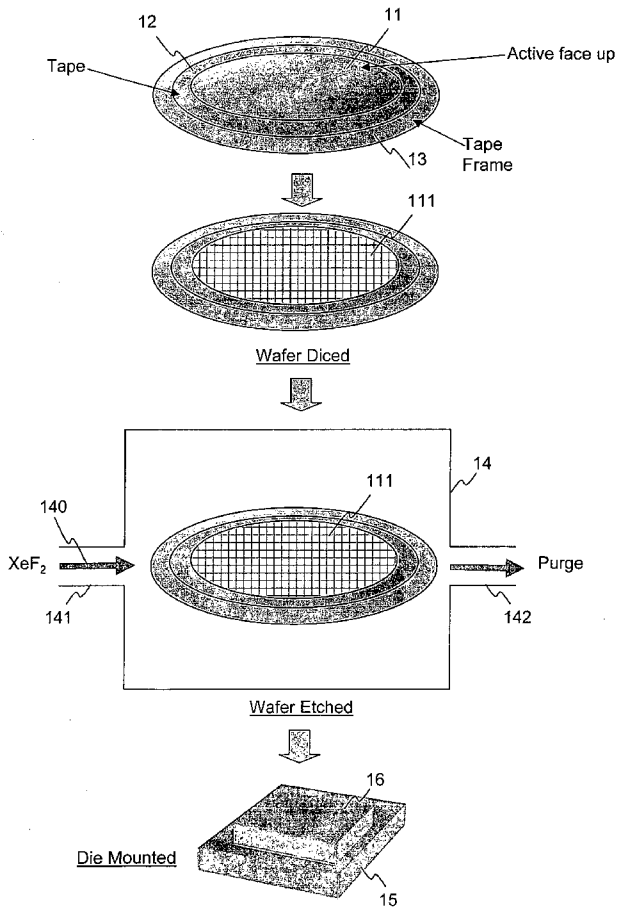
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(54) Title: INCREASING DIE STRENGTH BY ETCHING DURING OR AFTER DICING



(57) Abstract: A semiconductor wafer 11 having an active layer is mounted on a carrier 13 with the active layer away from the carrier and at least partially diced on the carrier from a major surface of the semiconductor wafer. The at least partially diced semiconductor wafer is etched on the carrier from the said major surface with a spontaneous etchant 140 to remove sufficient semiconductor material from a die produced from the at least partially diced semiconductor wafer to improve flexural bend strength of the die by removing at least some defects caused by dicing.

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